

Wednesday AM June 23, 2010		Wednesday AM June 23, 2010		Wednesday AM June 23, 2010	
EMC Student Awards and Plenary Lectures Room: Jordan Auditorium Mendoza College of Business		Session A: High-K Gate Dielectrics Room: 102		Session B: Non-Destructive Characterization Room: 126	
8:20 AM	Awards Ceremony	10:00 AM	A1, (Invited), The Electrical Properties of Metal/Gd ₂₀₃ Si Gate Stacks and Their Dependence on the Structure of the Oxide LayerMoshe Eizenberg	10:00 AM	B1, Innovative Time-Resolved Optical Characterization Techniques for Monitoring of Carrier Dynamics in Wide Band Gap SemiconductorsKestutis Jarasiunas
				10:20 AM	B2, Raman Characterization Methodologies Suitable for Determining Graphene Thickness and UniformityDavid Tomich
8:30 AM	(Plenary), Epitaxial Graphene: Designing a New Electronic MaterialWalter A. de Heer	10:40 AM	A2, (Student), Spin Dependent Trap Assisted Tunneling in Gd ₂ O ₃ DielectricsBrad Bittel	10:40 AM	B3, (Student), Characterizing the RF Properties of Semiconductors under Optical IlluminationYoussef Tawk
		11:00 AM	A3, Crystalline Lattice-Matched Ba _{0.7} Sr _{0.3} O on Si(001) as Gate DielectricHerbert Pfnür	11:00 AM	B4, (Student), Admittance Spectroscopy of GaSb(100) and ALD / PEALD Al ₂ O ₃ Dielectric Interface with Various Surface TreatmentsAshkar Ali
9:20 AM	Break	11:20 AM	A4, (Student), Rare-Earth Scandates/Tin Gate Stack on High Mobility Strained SOI for Fully Depleted (FD) MosfetsEylem Durgun Özben	11:20 AM	B5, (Student), High Temperature Coefficient of Resistance Sputtered A-Ge for Uncooled Microbolometer ApplicationsHang-Beum Shin
		11:40 AM	A5, Late News	11:40 AM	B6, (Student), Temperature Dependence of the Lattice Constant of Popular III-Sb Binary and Quarternary AlloysMagnus Breivik

Session Listing

Wednesday AM June 23, 2010		Wednesday AM June 23, 2010		Wednesday AM June 23, 2010	
Session C: Nanoscale Characterization Room: 129		Session D: Narrow Bandgap Semiconductor Bulk Materials and Devices Room: 131		Session E: Materials Integration: Wafer Bonding Room: 138	
10:00 AM	C1, (Student), Pulsed-Laser Atom Probe Tomographic Analysis of Ge-Ge/Co/Mn Thin-Film SuperlatticesJames Riley	10:00 AM	D1, (Invited) Review of Narrow Bandgap Semiconductor Based THz-EmittersIngrid Wilke	10:00 AM	E1, (Student), Investigation of Physisorbed and Chemisorbed Sulfur Species for GaAs Wafer BondingMichael Jackson
10:20 AM	C2, (Student), Atomic Scale Gate Electrode Formed by a Charged Defect on GaAs(110)Donghun Lee	10:20 AM	D2, (Student), Electrical and Optical Studies of Melt Grown Optical Grade InAs _{1-y} P _yJean Wei	10:20 AM	E2, (Student), AlGaAs/GaAs/GaN Wafer Fused HBTs with Ar Implanted Extrinsic CollectorsZongyang Hu
10:40 AM	C3, Ordered Assemblies of Bimetallic Nanostructure Arrays Utilizing a Self-assembled Disilicide Nanowire TemplateTalin Ayvazian	10:40 AM	D3, (Student), Electrical and Optical Properties of Bulk Ternary In _x Ga _{1-x} AsAustin Berstrom	10:40 AM	E3, (Student), Effect of Surface Activation for Ge-Si Integration Using Wafer BondingKi Yeol Byun
11:00 AM	C4, (Student), Scanned Probe Characterization of Self-Assembled ErAs/GaAs Semimetal/Semiconductor Nanostructures Grown by Molecular-Beam EpitaxyKeun Woo Park	11:00 AM	D4, (Student), Optical and Thermal Properties of III-V Bulk Ternary In _x Ga _{1-x} Sb and In _x Ga _{1-x} As CrystalsShekhar Guha	11:00 AM	E4, (Student), Strain, Annealing, and Exfoliation in Hydrogen Implanted GaN for Layer Transfer ApplicationsEric Padilla
11:20 AM	C5, Late News	11:20 AM	D5, Late News	11:20 AM	E5, Optimization of Adhesive Wafer Bonding for SiliconSue Holl
11:40 AM	C6, Late News	11:40 AM	D6, Late News	11:40 AM	E6, Development of Surface Activation Based Nano-Bonding and Interconnect SystemMatiar Howlader

Wednesday AM June 23, 2010		Wednesday PM June 23, 2010		Wednesday PM June 23, 2010	
Session F: Silicon Carbide Devices Room: 155		Session G: Oxide Semiconductor Thin Film Transistors Room: 102		Session H: Materials and Devices for Flexible Electronics Room: 126	
10:00 AM	F1, (Invited), Applications of SiC Power Devices – A Materials and Device PerspectiveAnant Agarwal	1:30 PM	G1, (Student), Temperature Dependent Measurements of ZnO TFTsDevin Mourey	1:30 PM	H1, (Student), Molecular Contact Doping in Organic Thin-Film TransistorsFrederik Ante
		1:50 PM	G2, (Student), Flexible ZnO Temperature Sensors on Plastic SubstrateDalong Zhao	1:50 PM	H2, (Student), Gate Dielectric Thickness Dependence of OTFT PerformanceYuanyuan Li
10:40 AM	F2, Review of the Dominant Scattering Mechanisms in SiC MOS DevicesJody Fronheiser	2:10 PM	G3, (Student), Improvement of InGaZnO ₄ TFT Device Performance on Glass and Paper SubstratesErica Douglas	2:10 PM	H3, (Student), Arylene Diimide-Thiophene Semiconductors for n-Channel Field-Effect TransistorsRocio Ponce Ortiz
11:00 AM	F3, (Student), A Comparative Study of Thermal and Deposited Gate Oxides on 4H SiCSarah Haney	2:30 PM	G4, Sputtering of ZnO Thin Films for TFT on Polyimide SubstratesFaraz Khan	2:30 PM	H4, (Student), Advanced X-Ray Peak Shape Analysis of Organic Semiconductors: Insights into Crystalline Size, Strain, Intragrain Disorder and Implications for Charge TransportJonathan Rivnay
11:20 AM	F4, (Student), Magnetic Resonance Studies of 4H SiC MOS StructuresBrad Bittel	2:50 PM	G5, (Student), Zinc-Tin-Oxide Thin-Film Transistors with Al ₂ O ₃ and ZrO ₂ Gate DielectricsJosh Triska	2:50 PM	H5, Probing Stress Effects in Single Crystal Organic Transistors by Scanning Kelvin Probe MicroscopyLucile Teague
11:40 AM	F5, Influence of Geometry on Silicon Carbide JBS Diodes ConductionMaxime Berthou	3:10 PM	Break	3:10 PM	Break
		3:30 PM	G6, (Student), Study of CV and Admittance Characteristics of ALD High-K Dielectric ZnO CapacitorsJeffrey Siddiqui	3:30 PM	H6, (Student), Study on the Resistance of Stretchable Electrodes from Surface Morphology Aided by Computer ModelingWenzhe Cao
		3:50 PM	G7, (Student), Transparent Rectifying Contacts - A New Concept for Transparent ElectronicsAlexander Lajnl	3:50 PM	H7, (Student), Reverse Offset Roll Printing Using High Resolution Printing Plate for Electronic ApplicationNackbong Choi
		4:10 PM	G8, Transition from Hopping to Band-like Transport in Solution-Processed Amorphous Zinc Tin Oxide Thin-Film TransistorsChen-Guan Lee	4:10 PM	H8, (Student), A Novel Hybrid Electrical and Chemical Barrier Material for Flexible ElectronicsLin Han
		4:30 PM	G9, (Student), A Comparative Study of the Effect of Heat Treatment on the Microstructure and Properties of Colloidal ITO Films and Cold-Sputtered ITO FilmSalil Joshi	4:30 PM	H9, (Student), Heavily Doped ZnO Thin Films for Hybrid Inorganic Organic DevicesZaheer Khan
		4:50 PM	G10, Optimization of Dielectric Passivation of ZnO-Based Schottky DiodesHolger von Wenckstern	4:50 PM	H10, Late News

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Wednesday PM June 23, 2010		Wednesday PM June 23, 2010		Wednesday PM June 23, 2010	
Session I: Nanomagnetic and Spintronic Materials Room: 129		Session J: Thin Film Photovoltaics Room: 131		Session K: III-Nitride Nanowires Room: 138	
1:30 PM	I1, An Organic-based Magnetic/Nonmagnetic Semiconductor as a Spin Polarized Carrier Source/Channel: Moving Toward Organic SpintronicsJung-Woo Yoo	1:30 PM	J1, MBE Growth of Metamorphic InGaP on GaAs and GaP for Wide-Bandgap Photovoltaic JunctionsJohn Simon	1:30 PM	K1, Molecular Beam Epitaxy of Catalyst-free InGaN/GaN Nanowires on (001) Silicon and Nanowire Light Emitting DiodesWei Guo
1:50 PM	I2, (Student), Effect of Perpendicular Magnetic Anisotropy on Emerging Magnetic Logic DevicesLarkhoon Leem	1:50 PM	J2, (Student), In _x Ga _{1-x} As Metamorphic Buffer Layers for Lattice Mismatched Multi-Junction Solar CellsPeter Dudley	1:50 PM	K2, Photoluminescence of Bandgap-Graded Ingan Wires Grown by Molecular Beam EpitaxyVladimir Protasenko
2:10 PM	I3, (Student), Observation of Antiferromagnetic Interlayer Exchange Coupling in a GaMnAs/GaAs:Be/GaMnAs tri-layerJonathan Leiner	2:10 PM	J3, (Student), Quantum Dot n-i-p-i Photovoltaic DevicesMichael Slocum	2:10 PM	K3, Growth of Dislocation-Free and High-Indium-Content InGaN/GaN Coaxial NanowiresQiming Li
2:30 PM	I4, Electrical Spin Injection in a Hybrid Organic/Inorganic Spin-Polarized Light Emitting Diode (Spin-LED)Ezekiel Johnston-Halperin	2:30 PM	J4, Characterization of a <I>p-i-n</I> Photovoltaic Cell Containing InAs/GaAs Quantum DotsAndrey Semichaevsky	2:30 PM	K4, Threshold Studies of Optically Pumped GaN Nanowire LasersJohn Schlager
2:50 PM	I5, Properties of MnAs/GaMnAs/MnAs Magnetic Multilayers and Their Application to High Temperature Vertical Spin ValvesDebashish Basu	2:50 PM	J5, MBE growth of lattice-matched 6.1 Å II-VI on GaSb substratesXinyu Liu	2:50 PM	K5, GaN Nanowire MOSFETs with Fully Conformal Cylindrical GatesPaul Blanchard
3:10 PM	Break	3:10 PM	Break	3:10 PM	Break
3:30 PM	I6, (Student), The Magneto-Optic Kerr Effect (MOKE) as a Measure of Strain-Induced Ferromagnetism in EuTiO ₃ Grown by Molecular-Beam EpitaxyLei Fang	3:30 PM	J6, ZnO/ZnTeO/ZnTe Heterojunctions for Intermediate State Solar CellsWeiming Wang	3:30 PM	K6, Formation Mechanisms and Kinetics of Negative Nanowires in GaN and ZnO Using In-Situ Transmission Electron MicroscopesBong-Joong Kim
3:50 PM	I7, (Student), Magnetic Circular Dichroism (MCD) studies on GaMnAsK r i t s a n u Tivakornsasithorn	3:50 PM	J7, (Student), Copper Zinc Tin Sulfide Solar Cell Development by RF Sputtering from Binary TargetsJeffrey Johnson	3:50 PM	K7, (Student), Self-Assembled GaN/AlN Nanowire Superlattices on Si toward Non-Polar Intersubband PhotonicsSantino Carnevale
4:10 PM	I8, (Student), Magneto-Optical Spectroscopy of MOVPE grown Ferromagnetic SemiconductorsMithun M. Bhowmick	4:10 PM	J8, (Student), Chemical Vapor Deposition of CsSnI ₃ Thin Films for Photovoltaic ApplicationsNicholas LiCausi	4:10 PM	K8, HVPE Homoepitaxy of p-type GaN on n-type Catalyst Free GaN NanowiresAric Sanders
4:30 PM	I9, Micromagnetic Simulation of Focused Ion Beam Patterned Cobalt-Platinum MultilayersGyorgy Csaba	4:30 PM	J9, (Student), Exploring More Effective Catalysts for Metal-Induced Growth of Thin Film SiPeter Mersich	4:30 PM	K9, Homoepitaxial Nucleation of GaN Nanowires in GroovesAlexana Roshko
4:50 PM	I10, (Student), Growth and Characterization of In _{1-x} Mn _x Sb Ferromagnetic Semiconductor Alloys using Metal Organic Vapor Phase Epitaxy (MOVPE)Caitlin Feeser	4:50 PM	J10, (Student), Enhanced Light Absorption in Thin-Film Silicon Solar Cells by Scattering from Sub-Surface Dielectric NanoparticlesJames Nagel	4:50 PM	K10, Growth and Lift-Off of High-Quality GaN Thin Films Using Self-Assembled Silica Microsphere MonolayersQiming Li

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Session L: III-N HEMTs I Room: 155		Session M: Graphene - Materials and Characterization Room: 102		Session N: Molecular Electronics and Chem / Bio Sensors Room: 126	
1:30 PM	L1, Formation of Structural Defects in AlGaIn/GaN High Electron Mobility Transistors under Electrical StressPrashanth Makaram	8:20 AM	M1, (Invited), Material and Electronic Properties of CVD Graphene grown on Ni and Cu then Transferred to InsulatorsYong Chen	8:20 AM	N1, STM Studies of Hybrid Inorganic-Organic Molecular Magnets on an Ultrathin Insulating FilmTaeyoung Choi
1:50 PM	L2, (Student), Electrical Properties of GaN/AlN/GaN Heterostructures: Presence of 2DHGSatyaki Ganguly			8:40 AM	N2, (Student), Effect of Molecular Tilt Configuration and Interface Dipoles on Molecular Electronic ConductionGunuk Wang
2:10 PM	L3, (Student), Study of Cause of G_m -Collapse for Higher Gate Voltages in N-Polar GaN HEMTs with Scaled GaN ChannelsNidhi Nidhi	9:00 AM	M2, Fabrication and Characterization of Graphene Materials Grown via CVD on Copper Based SubstratesMichelle Kelly	9:00 AM	N3, (Student), Improvement of Transfer Characteristics in Carbon Nanotube Field-Effect Transistors with Au Nano ClustersYasuki Yamamoto
2:30 PM	L4, (Student), Polarization-Engineered Low-Leakage Buffers for Nitride HEMTs Grown by MBEYu Cao	9:20 AM	M3, (Student), Kinetic Limitations in the Formation of Graphene on the C-face of SiCLuxmi Luxmi	9:20 AM	N4, Carbon Nanotube Field-Effect Transistor Biosensor with Schottky Barrier Control Gate ElectrodeMasuhiro Abe
2:50 PM	L5, (Student), The Influence of High-k Gate Dielectrics on Deep Traps in AlGaIn/GaN High Electron Mobility Transistors Measured by Deep Level Spectroscopy MethodsQilin Gu	9:40 AM	M4, (Student), Graphene to Graphane: Novel Electrochemical Conversion and Possible ApplicationsKevin Daniels	9:40 AM	N5, (Student), Breakdown Statistics and Nanowire Device Integration of Self-Assembled Nano DielectricsRuth Anne Schlitz
3:10 PM	Break	10:00 AM	Break	10:00 AM	Break
3:30 PM	L6, PECVD-SiN _x , Si or Si/Al ₂ O ₃ -Capped ED-Mode AlN/GaN InvertersTom Zimmermann	10:20 AM	M5, Growth of Few Layer Graphene on C-Face SiCVirgil Shields	10:20 AM	N6, Functionlization Studies on GaN NanowiresDevin Rourke
3:50 PM	L7, Late News	10:40 AM	M6, Graphene Growth on SiC, SiO ₂ , and Sapphire with Carbon AdditionJeonghyun Hwang	10:40 AM	N7, (Student), Olefin Metathesis Reaction on GaN (0001) SurfacesMatthew Makowski
4:10 PM	L8, Demonstration of Enhancement Mode AlN/Ultrathin AlGaIn/GaN HEMTs Using Selective Wet EtchingTravis Anderson	11:00 AM	M7, Ultrafast Transient Absorption Microscopy Studies of Carrier Dynamics in Epitaxial GrapheneLibai Huang	11:00 AM	N8, (Student), Protection of ZnO Nanowires for Liquid-Phase SensingAshley Mason
4:30 PM	L9, (Student), Growth and Characterization of InGaIn Heterojunction Bipolar TransistorsZachary Lochner	11:20 AM	M8, Comparison of Graphene Thickness Determination for MBE Grown Graphene on SiC using Raman, XPS, and TEMDavid Tomich	11:20 AM	N9, (Student) Signal-to-Noise Ratio Improvement of Magnetoelectric Laminate Sensor by Multilayer Structure and Direct Integration with Advanced MicroelectronicsZhao Fang
4:50 PM	L10, (Student), High Temperature Transport Properties of GaN HEMTs with Various Heterostructure DesignsRonghua Wang	11:40 AM	M9, Late News	11:40 AM	N10, Late News

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Thursday AM June 24, 2010		Thursday AM June 24, 2010		Thursday AM June 24, 2010	
Session O: SiC: Characterization and Growth Room: 129		Session P: One-Dimensional Photovoltaics Room: 131		Session Q: Oxide Thin Films Room: 138	
8:20 AM	O1, Analysis of Dislocation Interactions in Low Dislocation Density, PVT-Grown, Four-Inch Silicon Carbide Single Crystals Michael Dudley	8:20 AM	P1, Fabrication of Individual Silicon Nanowire Radial Junction Solar Cells Chito Kendrick	8:20 AM	Q1, Pulsed-dc Reactive Sputtering Vanadium Oxide Thin Films for Microbolometers Bharadwaja Srowthi
8:40 AM	O2, Formation of a (5-1)-Bilayer-Height Complex Step-and-Terrace Structure on 4H-SiC (0001) by a Spiral Etching Process..... Jun Suda	8:40 AM	P2, Wire Textured Multicrystalline Silicon Solar Cells Kejia Wang	8:40 AM	Q2, (Student), Defects in Low- κ ; Dielectrics and Etch Stop Layers for Use as Interlayer Dielectrics in ULSI Brad Bittel
9:00 AM	O3, Processes Controlling the Carrier Lifetime in n ⁺ 4H-SiC Epilayers with low $Z_{1/2}$ Concentrations Paul Klein	9:00 AM	P3, Efficiency Enhancements for Copper Contaminated Radial p-n Junctions over Planar p-n Junctions in Silicon Alec Talin	9:00 AM	Q3, (Student), Nanocluster and Nanocrystalline Si Trap Distributions within SiO ₂ /SiO _x /SiO ₂ Field Oxides for Radiation-Tolerant Electronics Evan Katz
9:20 AM	O4, Comparative Studies of Carrier Dynamics in 3C-SiC Layers Grown on Si and 4H-SiC Substrates Jawad Ul Hassan	9:20 AM	P4, (Student), Wafer Scale Si Nanowire Arrays for Photovoltaic Applications Yi Jing	9:20 AM	Q4, (Student), Nanoscale Depth-Resolved Electronic Properties of HfO ₂ /RPAN/Ge and HfSiON/RPAN/Ge Gate Dielectrics for Radiation-Tolerant Electronics Zhichun Zhang
9:40 AM	O5, Expansion and Contraction of Stacking Faults in 4H-SiC Nadeemullah Mahadik	9:40 AM	P5, Late News	9:40 AM	Q5, (Student), Nano-Gap Electrodes Formed at the Exposed Edge of Au/Al ₂ O ₃ /Au Tunnel Structures Grown by Atomic Layer Deposition Bing Hu
10:00 AM	Break	10:00 AM	Break	10:00 AM	Break
10:20 AM	O6, Influence of Stacking Fault Generation and Half Loop Array on Electrical Behavior of 4H-SiC 10 kV PiN Diodes Qingchun (Jon) Zhang	10:20 AM	P6, (Student), Branched ZnO/Si Nanowire Heterostructure Based Photoelectrochemical Cell for Efficient Water Splitting Ke Sun	10:20 AM	Q6, (Student), Surface-Interface Conductivity in Thin Film Gd-doped CeO ₂ Matthew Swanson
10:40 AM	O7, Reducing Basal Plane Dislocation Density in Nitrogen and Aluminum Doped 4H-SiC Epilayers Virginia Wheeler	10:40 AM	P7, Solar Cells Based on ZnO/ZnS Core-Shell Nanowires Arrays Aurelien Du Pasquier	10:40 AM	Q7, Growth of Heteroepitaxial SrRuO ₃ Electrodes on CeO ₂ Buffered R-Plane Al ₂ O ₃ Substrates by RF Magnetron Sputtering Madhana Sunder
11:00 AM	O8, Improved Surface Morphology of 4H-SiC Homoepitaxial Layers Grown on Si-Face 4° off-Axis Substrates Swapna Sunkari	11:00 AM	P8, (Student), Fabrication of Subwavelength Pillar Arrays on GaAs by Confined Self-Assembly Technique for Broadband Antireflection Coating Dae-Seon Kim	11:00 AM	Q8, (Student), Evidence of Ferroelectricity Induced by Epitaxial Strain in Calcium Titanate Thin Films Grown by Molecular-Beam Epitaxy Charles Brooks
11:20 AM	O9, (Student), High-Purity Semi-Insulating 4H-SiC Homoepitaxy at a High Growth Rate Using Dichlorosilane for High Power Devices Iftekhar Chowdhury	11:20 AM	P9, (Student), Hybrid Solar Cell Based on Patterned Nanopillar/P3HT Heterojunction Giacomo Mariani	11:20 AM	Q9, Synchrotron Spectroscopy Detection of Spin-Polarized Bands and Hopping-Induced Mixed Valence for Ti and Sc in GdSc _{1-x} Ti _x O ₃ for x = 0.18 and 0.25 Gerald Lucovsky
11:40 AM	O10, Vanadium Doping using VCl ₄ Source during the Chloro-Carbon Epitaxial Growth of 4H-SiC Yaroslav Koshka	11:40 AM	P10, Dissociation of Photo-Generated Excitons on Carbon Nanotubes at Type-II Heterojunctions Dominick Bindl	11:40 AM	Q10, Application of Many Electron Charge Transfer Multiplet (CTM) Theory to Band Edge and Band Defect States in High-K Gate Dielectrics and Complex Functional Oxide Thin Films Gerald Lucovsky

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Session R: ZnO Growth and Doping Room: 141		Session S: Light Emitting Diodes and Laser Diodes Room: 155		Session U: Graphene and Nanotubes - Devices Room: 102	
8:20 AM	R1, (Student), Nucleation Layer Based Optimization of MOCVD Grown ZnO by In Situ Laser Interferometry Jens-Peter Biethan	8:20 AM	S1, Effect of InAlN Electron Blocking Layer in Visible Light-Emitting Diodes on Quantum Efficiency Grown by Metalorganic Chemical Vapor Deposition Hee Jin Kim	1:30 PM	U1, (Student), Sub-20 nm Patterning of Graphene Nanoconstrictions Using Nanosphere Lithography and Characterization of Its Electronic Properties Nathaniel Safron
8:40 AM	R2, (Student), Influence of Substrate Temperature and Post-Deposition Anneal on Material Properties of Ga-Doped ZnO Prepared by Pulsed Laser Deposition Robin Scott	8:40 AM	S2, (Student), Fabrication of GaN-based Laser Diode and Laser Diode Facet Formation Wenting Hou	1:50 PM	U2, (Student), Carrier Transport in Graphene P-N Junctions Tian Fang
9:00 AM	R3, Epitaxial Electrochemical-Deposition of ZnO on Graphite and p-GaN Substrates Kazuyuki Uno	9:00 AM	S3, Performance Improvement of AlInGaN Visible Laser Diodes by Epitaxial Layer Design Jianping Liu	2:10 PM	U3, Epitaxial Graphene Materials Integration: Effects of Dielectric Overlayers on Structural and Electronic Properties Joshua Robinson
9:20 AM	R4, (Student), Control of ZnO Epitaxial Growth via Focused Ion Beam Induced Damage in Lattice-Mismatched Substrates Blake Stevens	9:20 AM	S4, (Student), Enhancement of the Light-extraction Efficiency of GaN-based Light-emitting Diodes using a Graded-Refractive-Index Layer Byung-Jae Kim	2:30 PM	U4, Comparison of Ballistic Performance of Graphene and Planar III-V MOSFETs for RF Low Voltage Applications Lingquan (Dennis) Wang
9:40 AM	R5, Properties of Nitrogen Molecules in ZnO Norbert Nickel	9:40 AM	S5, (Student), Nano-Fabrication of Green AlGaInN LEDs – Structural Wavelength Control and Enhanced Light Extraction Christoph Stark	2:50 PM	U5, Graphene Fundamental Trade-offs and Asymmetric Bandgap Opening Frank Tseng
10:00 AM	Break	10:00 AM	Break	3:10 PM	Break
		Session T: AlGaIn Growth and Devices Room: 155			
10:20 AM	R6, High-Quality p-Type ZnO Layers Grown by Co-Doping of N and Te Seunghwan Park	10:20 AM	T1, (Student), Polarization Induced p-Doped Nitride Quantum Well UV LEDs Jai Verma	3:30 PM	U6, Hall Effect Mobility of Epitaxial Graphene on Si-Face SiC Shin Mou
10:40 AM	R7, Magnetic Properties of Mn and N Doped ZnO Mathrubhutham Rajagopalan	10:40 AM	T2, Structural Characterization of Highly Conducting Al _x Ga _{1-x} N (x > 50%) for Deep Ultraviolet Light Emitting Diode Joseph Dion	3:50 PM	U7, (Student), Highly Efficient Photovoltaic Devices with Transparent Graphene Electrode and TiO ₂ Layer Minhyeok Choe
11:00 AM	R8, Effects of p-Type Doping on the ZnO Based Diluted Magnetic Semiconductor Thin Films Liping Zhu	11:00 AM	T3, Epitaxial Growth and Doping of AlGaIn alloys on AlN Single Crystal Substrates Ramón Collazo	4:10 PM	U8, (Student), Integrated Circuits Based on Carbon-Nanotube Transistors and Amorphous-Carbon Thin-Film Load Resistors Hyeyeon Ryu
11:20 AM	R9, (Student), Hydrothermal Synthesis of Wide Bandgap Be _{1-x} Zn _x O Nanorods for Solar Blind Photodetection Ke Sun	11:20 AM	T4, (Student), Morphological Development of Homoepitaxial AlN Thin Films Grown by MOCVD Anthony Rice	4:30 PM	U9, Late News
11:40 AM	R10, (Student), Synthesis and Characterization of p-NiO/n-ZnO Heterojunction Diode by Spray Pyrolysis Namseok Park	11:40 AM	T5, (Student), Aluminum Gallium Nitride Alloys Grown via Metal Organic Vapor Phase Epitaxy using Digital Alloy Growth Technique L. Rodak	4:50 PM	U10, Late News

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Thursday PM June 24, 2010		Thursday PM June 24, 2010		Thursday PM June 24, 2010	
Session V: Quantum Dots, Boxes, and Wires Room: 126		Session W: Semiconducting and Metallic Nanowires Room: 129		Session X: Narrow Bandgap Semiconductors: Infrared Detectors and Lasers Room: 131	
1:30 PM	V1, Toward Conversion from Electron Pairs to Photon Pairs in Quantum Dots Ikuo Suemune	1:30 PM	W1, (Student), Single Crystalline Wurtzite GaAs Nanoneedles Epitaxially Grown on Highly Lattice-Mismatched Sapphire with Bright Luminescence Wai Son Ko	1:30 PM	X1, Minority Carrier Lifetime in LWIR Type II Superlattice Detector Structures Using Time-Resolved PhotoluminescenceBlair Connelly
1:50 PM	V2, Tensile-Strained Self-Assembled III-V Nanostructures Paul Simmonds	1:50 PM	W2, Twinning Superlattice in VLS Grown <110> Planar GaAs Nanowires Induced by Impurity Doping Xiuling Li	1:50 PM	X2, (Student), MOCVD Growth of InAs/GaSb Type-II Superlattice Structures and Photodiodes for Mid-Infrared Detection Yong Huang
2:10 PM	V3,(Student),Self-AssembledIn _{0.5} Ga _{0.5} As Quantum Dots on GaP(001) Yuncheng Song	2:10 PM	W3, (Student), Photoluminescence of InGaAs Nano-Pillar Arrays on GaAs Substrate Joshua Shapiro	2:10 PM	X3, (Student), Investigation of Passivation Techniques on InAs/GaSb Strained Layer Superlattice Long Wave Infrared Detectors Maya Narayanan Kutty
2:30 PM	V4, Late V4, (Student), Time-Resolved Spectroscopy of Single Colloidal CdSe Nanowires with Picosecond Resolution Joseph Herzog News	2:30 PM	W4, (Student), Synthesis and Characterization of GaAs/MnAs Core/Shell Nanowires Nicholas Dellas	2:30 PM	X4, (Student), Investigation of Antimonide Infrared Detectors Based on the nBn Design Stephen Myers
2:50 PM	V5, Late News	2:50 PM	W5, (Student), Contact Laser Annealing Effects on Indium Oxide Nanowire Transistors Seongmin Kim	2:50 PM	X5, Late News
3:10 PM	Break	3:10 PM	Break	3:10 PM	Break
3:30 PM	V6, Resonant Periodic Gain InAs Quantum Dot VECSEL Alexander Albrecht	3:30 PM	W6, (Student), Vertical InSb Nanowire Arrays Electrodeposited into Porous Anodic Alumina Templates on Silicon Substrates Suprem Das	3:30 PM	X6, (Student), Quinary GaInAsSbP on GaAs Substrates Grown by Metal Organic Vapor Phase Epitaxy (MOVPE) Toby Garrod
3:50 PM	V7, Quantum Dot Light Emitting Devices and Exciton Recombination Zone Seonghoon Lee	3:50 PM	W7, (Student), High Growth Rate and Control of Staking Faults on InP Semiconductor Thalita Chiamonte	3:50 PM	X7, (Student), Growth of GaAs _{1-x} Bi _x /Al _y Ga _{1-y} As Multi-Quantum Well Structures on GaAs Takuma Fuyuki
4:10 PM	V8, (Student), Thermal Stability in Emission Peak in Multilayer InAs/GaAs Quantum Dot Heterostructure in Laser Application Subhananda Chakrabarti	4:10 PM	W8, Formation of Periodic Nanostructures through Kirkendall Constitutional Interdiffusion in Epitaxial Heterostructures Patrick Taylor	4:10 PM	X8, (Student), Perforated (In)GaSb Quantum Wells on GaSb Substrates through the Use of As ₂ Based In-Situ Etches P. Ahirwar
4:30 PM	V9, Enhancement of Luminescence Efficiency in InAs/GaAs Quantum Dots by Proton Irradiation Subhananda Chakrabarti	4:30 PM	W9, (Student), Thermal Conductivity of Aluminum Nanowires near Room Temperature: Direct Measurements and Theory Nenad Stojanovic	4:30 PM	X9, (Student), Antimonide VECSELs on AlGaAs DBRs T. J. Rotter
4:50 PM	V10, Late News	4:50 PM	W10, Simulation of the Influence of Grain Boundaries on Resistivity via the Wigner-Fokker-Planck Equation Richard Sharp	4:50 PM	X10, (Student), Effect of Aluminum Composition on Current-Voltage Characteristics of AlGaSb/InAs Tunnel Junction Yeqing Lu

Thursday PM June 24, 2010		Thursday PM June 24, 2010		Thursday PM June 24, 2010	
Session Y: III-N Nanostructures Room: 138		Session AA: Oxide Defects, Localized States, and Nanostructures Room: 141		Session BB: III-V Novel Electronic Devices Room: 155	
1:30 PM	Y1, (Student), Dislocation Filtering in GaN Nanorods Robert Colby	1:30 PM	AA1, Vacancy Defect and Defect Cluster Energetics in Ion-Implanted ZnO Leonard J. Brillson	1:30 PM	BB1, (Student), Demonstration and Room Temperature Electrical Characteristics of a Nitride Hot Electron Transistor with GaN Base of 10 nm Sansaptak Dasgupta
1:50 PM	Y2, (Student), Threading Defect Elimination in GaN NanostructuresAshwin Rishinaramangalam	1:50 PM	AA2, O-H-Li-Complex in Hydrothermally Grown Single Crystalline ZnO Klaus Magnus Johansen	1:50 PM	BB2, (Student), Novel Cs-free GaN Photocathodes Fatemeh (Shadi) Shahedipour-Sandvik
2:10 PM	Y3, (Student), Yellow-Orange Luminescence from III-Nitride Nanopyramid Heterostructures Isaac Wildeson	2:10 PM	AA3, Induced Gap States at Zinc Oxide Surfaces and Interfaces S.M. Durbin	2:10 PM	BB3, Influence of MOVPE Growth Conditions on Intersubband Absorption in AlN-AlGaN Superlattices Andrew Allerman
2:30 PM	Y4, (Student), Molecular Beam Epitaxial Growth and Characterization of InGaN/GaN Dot-in-a-Wire Nanoscale Heterostructures on Si..... Jiale Wang	2:30 PM	AA4, Optical Properties of Gd Implanted ZnO Single Crystals John Kennedy	2:30 PM	BB4, (Student), Engineering Ferromagnetism in Gd-Doped GaN Two-Dimensional Electron Gases Jing Yang
2:50 PM	Y5, (Student), Electrochemical Etching of GaN and Its Applications Yu Zhang	2:50 PM	AA5, High-Resolution Laplace DLTS on Mg _x Zn _{1-x} O PLD Thin Films Holger von Wenckstern	2:50 PM	BB5, Nearly Ideal Current-Voltage Characteristics of Schottky Barrier Diodes Directly Formed on GaN Free-Standing Substrates..... Jun Suda
3:10 PM	Break	3:10 PM	Break	3:10 PM	Break
Session Z: Point and Extended Defects and Doping in Wide Bandgap Materials Room: 138				Session CC: III-N HEMTs II Room: 155	
3:30 PM	Z1, Luminescence Recombination Dynamics of Ytterbium Implanted GaN Epilayers Jingzhou Wang	3:30 PM	AA6, (Student), Observation of a Strong Polarization Induced Quantum-Confined Stark Effect in Mg _x Zn _{1-x} O/Zno Quantum Wells Matthias Brandt	3:30 PM	CC1, (Student), High Al Composition Al _{0.72} Ga _{0.28} N/Aln/GaN Heterostructures with High Mobility Two-Dimensional Electron Gases Guowang Li
3:50 PM	Z2, Energy Levels of Nd ³⁺ Ions in <I>In Situ</I> Doped AlN Grace Metcalfe	3:50 PM	AA7, Low Temperature Electrochemical Growth of ZnO Nanobelts, Nanowalls, Nanospikes and Nanowires: Growth Mechanism and Field Emission Study Debabrata Pradhan	3:50 PM	CC2, (Student), Two-Dimensional Electron Gas in In _x Al _{1-x} N/Aln/GaN Heterostructure Field-Effect Transistors Depending on Indium Composition Suk Choi
4:10 PM	Z3, Correlation of InGaN Growth Parameters, Defects and MQW Radiative Efficiency for Blue to Green Emission Andrew Armstrong	4:10 PM	AA8, (Student), Synthesis and Field Emission Characterizations of Well-Aligned Single-Crystal Al-Doped Zno Nanowires Grown at Low Temperature Po-Yu Yang	4:10 PM	CC3, Source-Drain Regrowth by MBE in Metal-Face AlN/GaN HEMTs Chuanxin Lian
4:10 PM	Z4, (Student), Proton-Irradiated AlGaIn/GaN HEMT at 5 MeV Protons Hong-Yeol Kim	4:30 PM	AA9, (Student), Correlation of ZnO Polar Surface Nanostructure with Native Point Defects Tyler Merz	4:30 PM	CC4, (Student), AlGaIn/GaN High Electron Mobility Transistors for Large Current Operation Achieved by Selective-Area Growth Using Plasma-Assisted Molecular Beam Epitaxy Liang Pang
4:30 PM	Z5, Effect of Traps Spatial Localization on GaN HEMT Static Characteristics Alessandro Chini	4:50 PM	AA10, (Student), Evolution and Growth of Nanostructures on ZnO with Staged Annealing Daniel Doust	4:50 PM	CC5, Transport Studies of AlGaIn/GaN Heterostructures with Variable SiN _x Passivant Stress Giacinta Parish

Session Listing

Friday AM June 25, 2010		Friday AM June 25, 2010		Friday AM June 25, 2010	
Session DD: Oxide Semiconductor Heterojunction Diodes Room: 102		Session EE: Epitaxy Materials and Devices Room: 126		Session FF: Si and Ge Nanowires Room: 129	
8:20 AM	DD1, Ultraviolet Photodetectors with Novel Oxide Thin Films Shizuo Fujita	8:20 AM	EE1, (Student), Overgrowth Investigation of Epitaxial Semimetallic Nanoparticles for Photonic Devices Adam Crook	8:20 AM	FF1, (Student), The Influence of the Catalyst on Dopant Incorporation During Si and Ge Nanowire Growth Justin Connell
8:40 AM	DD2, (Student), Polarization-sensitive Schottky Photodiodes Based on A-plane ZnO/ZnMgO Multiple Quantum-wells Gema Tabares	8:40 AM	EE2, (Student), Regrown InGaAs Tunnel Junctions for TFETs Guangle Zhou	8:40 AM	FF2, Size Effects in Semiconductor Nanowire Synthesis at the Ultimate Limit Shadi Dayeh
9:00 AM	DD3, A New Approach to Make ZnO-Cu ₂ O Heterojunctions for Solar Cells Aurelien Du Pasquier	9:00 AM	EE3, (Student), Molecular Beam Epitaxy of Very Thin Fluoride Films on Ge(111) and its Application to Resonant Tunneling Diodes Keita Takahashi	9:00 AM	FF3, (Student), Growth and Applications of Silicon/Germanium Axial Nanowire Heterostructures Cheng-Yen Wen
9:20 AM	DD4, (Student), Double Heterojunction Metal-Semiconductor-Metal Photodetector Using ZnO/Si Structure Tingfang Yen	9:20 AM	EE4, (Student), Hole Mobility Improvement in Strained InGaSb Quantum Well with Carbon Doping Chichih Liao	9:20 AM	FF4, (Student), SiGe/Si Selective Etch Structures for Nanowire Release and Assembly Sharis Minassian
9:40 AM	DD5, (Student), A Study of Indium Doped-ZnO/p-Si(111) Diode Characteristics with Various In Mole Fraction Jong Hoon Lee	9:40 AM	EE5, (Student), Growth and Thermal Conductivity of Polycrystalline GaAs Grown on CVD Diamond using Molecular Beam Epitaxy Stephen Clark	9:40 AM	FF5, Diffusion Formation of Nickel Silicides Contacts in Silicon Nanowires Michael Beregovsky
10:00 AM	DD6, (Student), Effects of High - Energy Electron Irradiation on Pd/ZnO/Si MSM Photodetector: Conduction Mechanisms and Radiation Resistance Franklin Catalfamo	10:00 AM	Break	10:00 AM	Break
10:20 AM	Break	10:20 AM	EE6, Thick HVPE Growth of Patterned Semiconductors for Nonlinear Optics Candace Lynch	10:20 AM	FF6, (Student), Comparative Study of Ni-silicide and Germanide Formation in Contacts to Si and Ge Nanowires Nicholas Dellas
10:40 AM	DD7, Late News	10:40 AM	EE7, (Student), Effects of Carrier Localization on Emission Spectra of Dilute GaAsN Materials Doped with Silicon Yan He	10:40 AM	FF7, (Student), High Responsivity Vertical Si Nanowire Photodetector Arrays Yi Jing
11:00 AM	DD8, Late News	11:00 AM	EE8, (Student), Fabrication and Characterization of Free-Standing InGaAs/GaAs Quantum Dot Microbelt-like Optical Resonators Feng Li	11:00 AM	FF8, Si Nanowire Mats for Large-area Electronics William Wong
11:20 AM	DD9, Late News	11:20 AM	EE9, MBE Grown InGaAsSbN/GaSb Single Quantum Wells for Mid-Infrared Applications Sudhakar Bharatan	11:20 AM	FF9, Jet-printed and Dielectrophoretically Aligned Nanowires for Large Area Electronics Surobh Raychaudhuri
11:40 AM	DD10, Late News	11:40 AM	EE10, Late News	11:40 AM	FF10, Late News

Friday AM June 25, 2010		Friday AM June 25, 2010		Friday AM June 25, 2010	
Session GG: Thermoelectrics and Thermionics Room: 131		Session HH: Semiconductor Processing, Surfaces and Contacts Room: 138		Session II: Heteroepitaxy on Silicon Room: 141	
8:20 AM	GG1, (Student), Bulk-like Thermionic Energy Conversion Device Fabricated from Laminated Nanostructured Metal/Semiconductor Superlattices Jeremy Schroeder	8:20 AM	HH1, (Student), Effect of Contact Modification on Charge Transport at Different Length Scales in Poly(3-Hexylthiophene)-Based Bottom-Contact Field-Effect Transistors Kumar Singh	8:20 AM	II1, (Student), Reduction in Operation Voltage of Light Emitting Diodes Fabricated in Si/III-V-N/Si Heterostructure Keisuke Yamane
8:40 AM	GG2, (Student), Epitaxial Growth of Transition Metal Nitrides on MgO via DC Magnetron Sputtering Robert Wortman	8:40 AM	HH2, (Student), Low Pressure Chemical Vapor Deposition of Conformal Boron Thin Films on Deep RIE-Etched Si Substrates Nicholas LiCausi	8:40 AM	II2, GaN/AlN Heterostructures on Vertical {111} Fin Facets of Si (110) Substrates Mark Holtz
9:00 AM	GG3, (Student), Enhancement of Thermoelectric Efficiency in $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ Heterostructures Md Hossain	9:00 AM	HH3, (Student), Assessment of the Passivation Capabilities of Two Different Covalent Modifications on GaP (100) David Richards	9:00 AM	II3, (Student), 2 μm Thick Device Quality GaN on Si(111) Using AlGaIn Graded Buffer Benjamin Leung
9:20 AM	GG4, Isothermal Method for Rapid, Steady-State Measurement of Thermoelectric Materials and Devices Patrick Taylor	9:20 AM	HH4, (Student), Comparison of Ga-Polar and N-Polar GaN by KOH Photoelectrochemical Etching Younghun Jung	9:20 AM	II4, (Student), Compositionally-graded Layers Composed of Tandem InGaAs InGaP Alloys and Pure GaAsSb Alloys to Engineer the InP Lattice Constant on GaAs Substrates Li Yang
9:40 AM	GG5, Late News	9:40 AM	HH5, (Student), N-Type Electrodes for GaN-Based Vertical Light Emitting Diodes Tae-Yeon Seong	9:40 AM	II5, Characterization of Standard and Ferromagnetic Schottky Barriers on GaP/GaP and GaP/Si Epi-Layers Chris Ratcliff
10:00 AM	Break	10:00 AM	Break	10:00 AM	Break
10:20 AM	GG6, (Student), Thermomagnetic Transport Properties of $(\text{Ag}_x\text{SbTe}_{2-x})_{15}(\text{GeTe})_{85}$ Thermoelectric Materials Yi Chen	10:20 AM	HH6, (Student), In-situ Ohmic Contacts to p-InGaAs Ashish Baraskar	10:20 AM	II6, Silicon Nanostructures Ion Implanted with Carbon and Nitrogen as an Electron Emitting Device Damian Carder
10:40 AM	GG7, (Student), Thermoelectric Properties of Sn-Rich $\text{Pb}_{1-x}\text{Sn}_x\text{Te}$ Alloys Doped with Indium Yibin Gao	10:40 AM	HH7, (Student), Degradation of Ohmic and Schottky Contacts on InGaAs MHEMTs during Bias Stressing Erica Douglas	10:40 AM	II7, High-Quality (211)B CdTe on (211) Si Substrates Using Metal-Organic Vapor-Phase Epitaxy Sunil Rao
11:00 AM	GG8, (Student), Incorporation of AgSbTe_2 to $\text{Pb}_{1-x}\text{Sn}_x\text{Te}$ by Mechanical Alloying of End Compounds Aaron D. LaLonde	11:00 AM	HH8, (Student), Characterization of Thin InAlP Native Oxide Gate Dielectric Layers for GaAs MOSFET Applications Wangqing Yuan	11:00 AM	II8, (Student), Metalorganic Vapor Phase Epitaxial Growth of (211)CdTe on Nanopatterned (211)Ge/Si Substrates using Full Wafer Block Copolymer Lithography Shashidhar Shintri
11:20 AM	GG9, (Student), Electron Transport Properties of Mechanically Alloyed N-type $\text{Pb}_{1-x}\text{Sn}_x\text{Te}$ Thermoelectric Elements Lakshmi Krishna	11:20 AM	HH9, Post-Growth InGaAsP Quantum Well Intermixing for High Saturation Power Semiconductor Optical Amplifiers Jonathan Klamkin	11:20 AM	II9, (Student), Effects of Ex-Situ Cycle Annealing on Dislocation Densities of HgCdTe/CdTe/Si Layers Stuart Farrell
11:40 AM	GG10, Late News	11:40 AM	HH10, Late News	11:40 AM	II10, Late News

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Friday AM June 25, 2010	
Session JJ: Nonpolar-Semipolar III-Ns	
Room: 155	
8:20 AM	JJ1, (Student), Internal Quantum Efficiency of Polar and Non-Polar GaInN/GaN Multiple Quantum Wells Liang Zhao
8:40 AM	JJ2, (Student), Optical Polarization of Non-polar GaInN/GaN LEDs Shi You
9:00 AM	JJ3, (Student), Anisotropic Carrier Mobility in GaN Quantum Well Grown in Non-polar Direction: Polarization Induced Dipole and Interface Roughness Scattering Aniruddha Konar
9:20 AM	JJ4, MBE Growth of Nitrogen-Face Aluminum Nitride by Polarity Inversion Using Magnesium Overdoping Craig Moe
9:40 AM	JJ5, Electro-Thermo-Mechanical Simulation of AlGaIn/GaN HFETs and MOSHFETs Anusha Venkatachalam
10:00 AM	Break
Session KK: Indium Nitride	
Room: 155	
10:20 AM	KK1, Mg Doped InN and Search for P-type InN Ke Wang
10:40 AM	KK2, (Student), Dislocation Reduction via Epitaxial Lateral Overgrowth of InN by Selective-area-growth of RF-MBE Jumpei Kamimura
11:00 AM	KK3, Growth Orientation Control of InN by Pulsed eXcitation Deposition Hiroshi Fujioka
11:20 AM	KK4, (Student), Optical and Electrical Transport Properties of Nearly Intrinsic and Si-doped InN Nanowires Yi-Lu Chang
11:40 AM	KK5, (Student), Growth Optimization of Si_3N_4 on GaN by Metal-Organic Chemical Vapor Deposition Brian Swenson